

# MMBF5460LT1

## JFET - General Purpose Transistor

### P-Channel

#### Features

- Pb-Free Package is Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	$V_{DG}$	40	Vdc
Reverse Gate-Source Voltage	$V_{GSR}$	40	Vdc
Forward Gate Current	$I_{GF}$	10	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

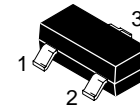
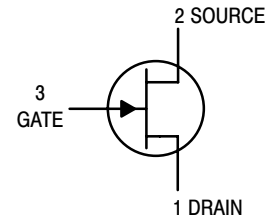
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.



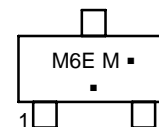
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236)  
CASE 318  
STYLE 10

#### MARKING DIAGRAM



M6E = Device Code  
M = Date Code\*  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBF5460LT1	SOT-23	3,000 / Tape & Reel
MMBF5460LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

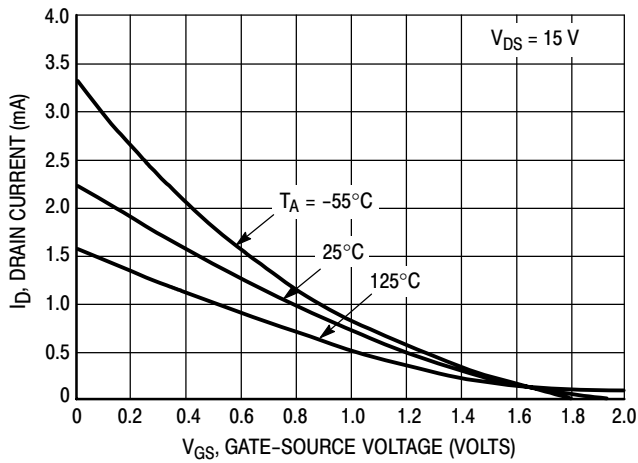
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBF5460LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

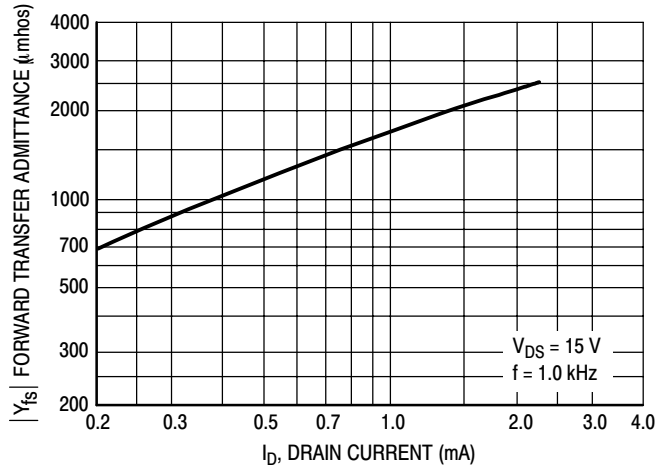
Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Gate–Source Breakdown Voltage ( $I_G = 10 \mu\text{Adc}$ , $V_{DS} = 0$ )	$V_{(BR)GSS}$	40	–	–	Vdc
Gate Reverse Current ( $V_{GS} = 20 \text{Vdc}$ , $V_{DS} = 0$ ) ( $V_{GS} = 20 \text{Vdc}$ , $V_{DS} = 0$ , $T_A = 100^\circ\text{C}$ )	$I_{GSS}$	–	–	5.0 1.0	nAdc $\mu\text{Adc}$
Gate Source Cutoff Voltage ( $V_{DS} = 15 \text{Vdc}$ , $I_D = 1.0 \mu\text{Adc}$ )	$V_{GS(off)}$	0.75	–	6.0	Vdc
Gate Source Voltage ( $V_{DS} = 15 \text{Vdc}$ , $I_D = 0.1 \text{mAdc}$ )	$V_{GS}$	0.5	–	4.0	Vdc
<b>ON CHARACTERISTICS</b>					
Zero–Gate–Voltage Drain Current ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ )	$I_{DSS}$	–1.0	–	–5.0	mAdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Forward Transfer Admittance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{kHz}$ )	$ Y_{fs} $	1000	–	4000	$\mu\text{mhos}$
Output Admittance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{kHz}$ )	$ Y_{os} $	–	–	75	$\mu\text{mhos}$
Input Capacitance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{MHz}$ )	$C_{iss}$	–	5.0	7.0	pF
Reverse Transfer Capacitance ( $V_{DS} = 15 \text{Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{MHz}$ )	$C_{rss}$	–	1.0	2.0	pF

**DRAIN CURRENT versus GATE SOURCE VOLTAGE**

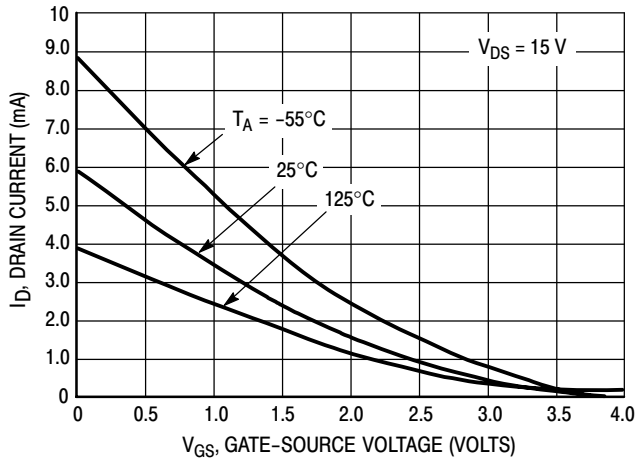


**Figure 1.  $V_{GS(off)} = 2.0$  Volts**

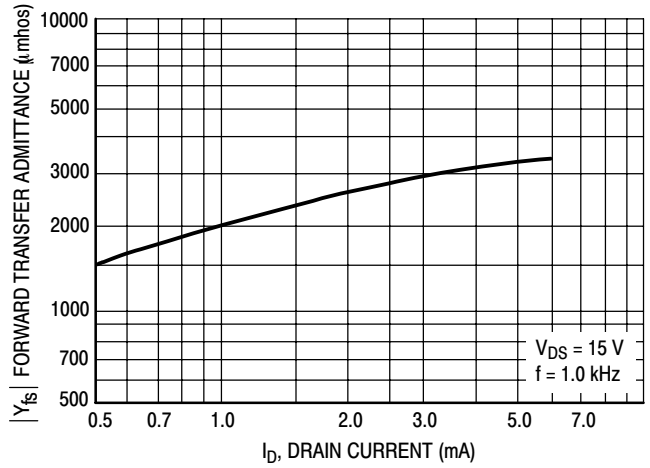
**FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT**



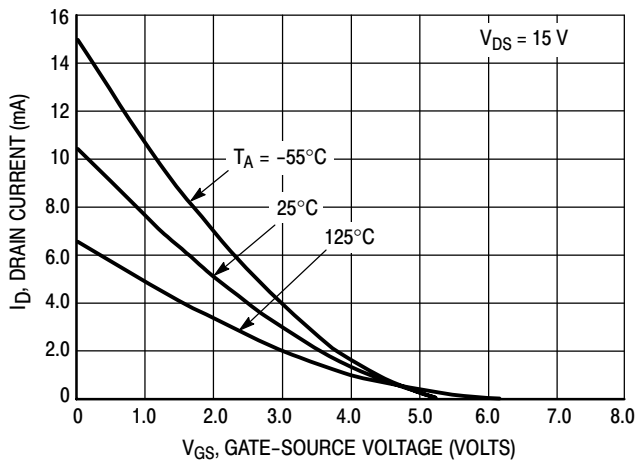
**Figure 4.  $V_{GS(off)} = 2.0$  Volts**



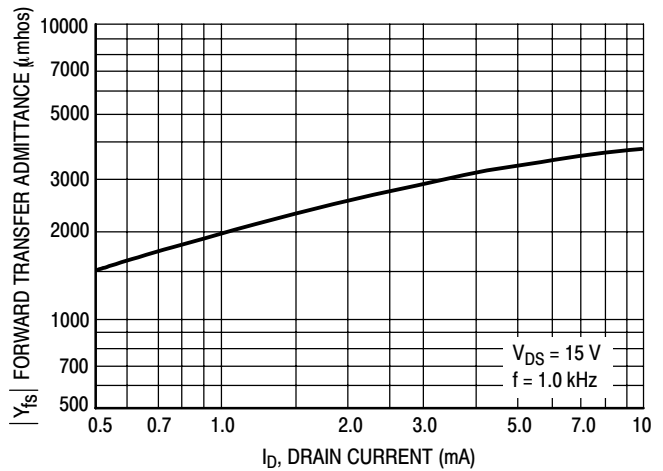
**Figure 2.  $V_{GS(off)} = 4.0$  Volts**



**Figure 5.  $V_{GS(off)} = 4.0$  Volts**

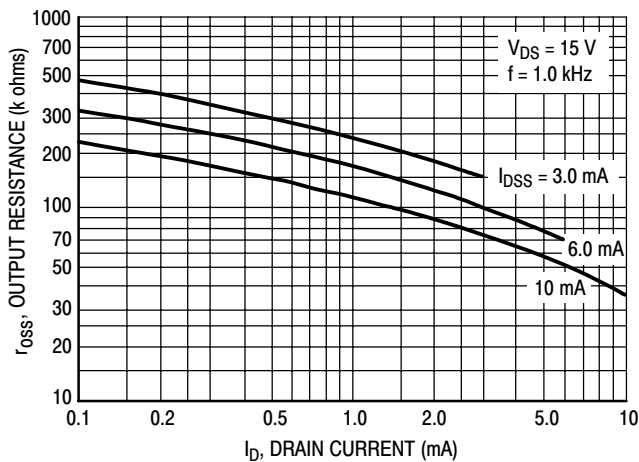


**Figure 3.  $V_{GS(off)} = 5.0$  Volts**

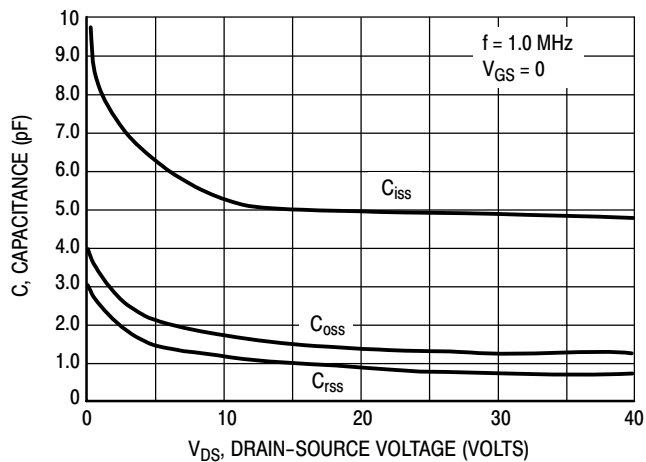


**Figure 6.  $V_{GS(off)} = 5.0$  Volts**

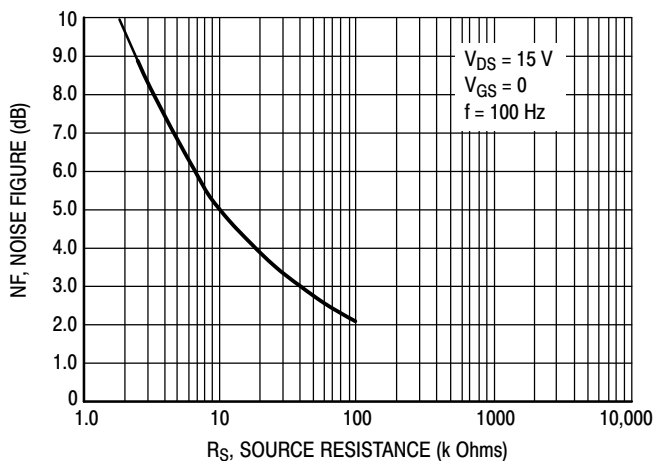
# MMBF5460LT1



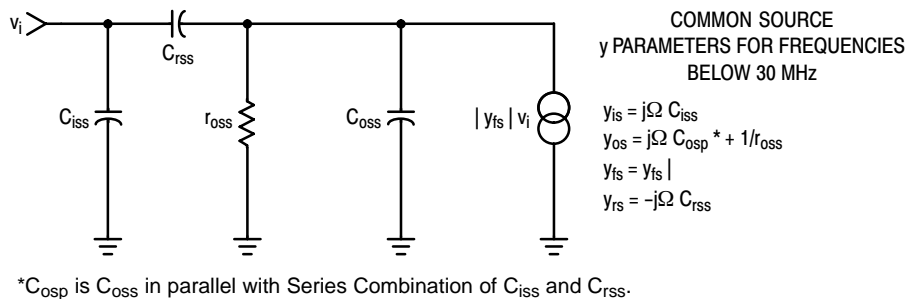
**Figure 7. Output Resistance versus Drain Current**



**Figure 8. Capacitance versus Drain-Source Voltage**



**Figure 9. Noise Figure versus Source Resistance**



NOTE:

- Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

**Figure 10. Equivalent Low Frequency Circuit**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**SOT-23 (TO-236)**  
**CASE 318-08**  
**ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |   |   |   |  |
|---|---|---|--|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

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